

TOSHIBA Diode Silicon Epitaxial Schottky Barrier Type

1SS367

High Speed Switching Application

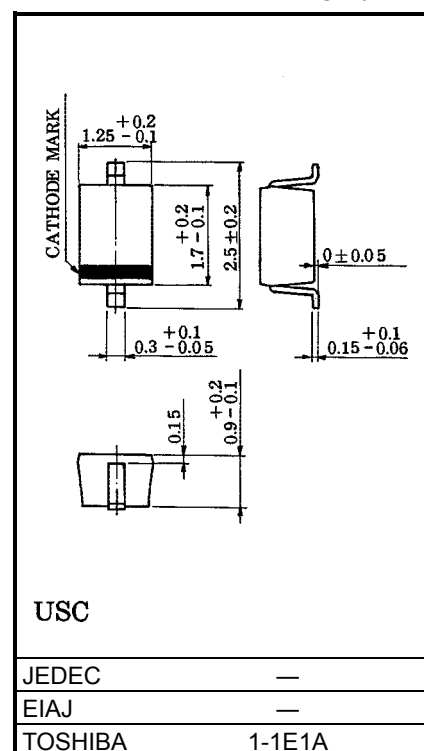
Unit: mm

- Small package
- Low forward voltage: $V_F = 0.23\text{V (typ.) @ } I_F = 5\text{mA}$

Maximum Ratings ($T_a = 25^\circ\text{C}$)

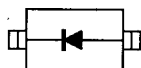
Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	15	V
Reverse voltage	V_R	10	V
Maximum (peak) forward current	I_{FM}	200	mA
Average forward current	I_O	100	mA
Surge current (10ms)	I_{FSM}	1	A
Power dissipation	P^*	200	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55~125	$^\circ\text{C}$
Operating temperature range	T_{opr}	-40~100	$^\circ\text{C}$

* Mounted on a glass epoxy circuit board of 20×20 mm
Pad dimension of 4×4 mm.

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_F (1)$	—	$I_F = 1\text{mA}$	—	0.18	—	V
	$V_F (2)$	—	$I_F = 5\text{mA}$	—	0.23	0.30	
	$V_F (3)$	—	$I_F = 100\text{mA}$	—	0.35	0.50	
Reverse current	I_R	—	$V_R = 10\text{V}$	—	—	20	μA
Total capacitance	C_T	—	$V_R = 0, f = 1\text{MHz}$	—	20	40	pF

Equivalent Circuit (Top View)



Marking

